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What Is Claimed Is:

1. A method of fabricating a liquid crystal display panel, comprising the steps of:
- preparing an upper substrate and a lower substrate;
 - bonding the upper substrate to the lower substrate;
 - cleaning exposed surfaces of the bonded upper and lower substrates; and
 - eliminating the exposed surfaces of the bonded upper and lower substrates.
2. The method according to claim 1, wherein the step of cleaning exposed surfaces includes dry-etching.
3. The method according to claim 1, wherein the step of eliminating the exposed surfaces includes wet-etching.
4. The method according to claim 1, further including the steps of:
- forming a thin film transistor on the lower substrate;
 - forming a protective layer on the lower substrate; and
 - forming a pixel electrode on the protective layer to electrically contact the thin film transistor.
5. The method according to claim 4, wherein the pixel electrode is formed

of a transparent conductive material including indium-tin-oxide (ITO), indium-zinc-oxide (IZO) and indium-tin-zinc-oxide (ITZO).

6. The method according to claim 4, wherein the protective layer is formed of an organic insulating material including an acrylic organic compound, Teflon⁷, benzocyclobutene (BCB), Cytop⁷ and perfluorocyclobutane (PFCB).

7. The method according to claim 4, wherein the step of forming the thin film transistor includes:

forming a gate electrode on the lower substrate;

forming a gate insulating film on the lower substrate to cover the gate electrode;

forming an active layer on the gate insulating film; and

forming a source electrode and a drain electrode on the active layer.

8. The method according to claim 7, wherein the source electrode and drain electrode contact the gate insulating film.

9. The method according to claim 7, wherein the pixel electrode contacts parallel and inclined surfaces of the drain electrode.

10. A method of fabricating a liquid crystal display panel, comprising the

steps of:

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bonding an upper substrate to a lower substrate;
 cleaning exposed surfaces of the bonded upper and lower substrates; and
 removing the exposed surfaces of the bonded upper and lower
 substrates.

11. The method according to claim 10, wherein the step of cleaning exposed
 surfaces includes dry-etching.

12. The method according to claim 10, wherein the step of removing the
 exposed surfaces includes wet-etching.

13. The method according to claim 10, wherein the step of removing the
 exposed surfaces uniformly reduces a thickness of the liquid crystal display
 panel.

14. A method of fabricating a liquid crystal display panel, comprising the
 steps of:

forming a gate electrode on a lower substrate;

forming a gate insulating film on the lower substrate to cover the gate
 electrode;

forming an active layer on the gate insulating film; and

forming a source electrode and a drain electrode on the active layer;
bonding an upper substrate to the lower substrate;
cleaning exposed surfaces of the bonded upper and lower substrates; and
removing the exposed surfaces of the bonded upper and lower
substrates.

15. The method according to claim 14, wherein the step of cleaning exposed
surfaces includes dry-etching.

16. The method according to claim 14, wherein the step of removing the
exposed surfaces includes wet-etching.

17. The method according to claim 14, further including the steps of
forming a protective layer on the lower substrate; and
forming a pixel electrode on the protective layer to electrically
contact the drain electrode.

18. The method according to claim 17, wherein the pixel electrode is formed
of a transparent conductive material including indium-tin-oxide (ITO),
indium-zinc-oxide (IZO) and indium-tin-zinc-oxide (ITZO).

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19. The method according to claim 17, wherein the protective layer is formed of an organic insulating material including an acrylic organic compound, Teflon⁷, benzocyclobutene (BCB), Cytop⁷ and perfluorocyclobutane (PFCB).

20. The method according to claim 14, wherein the step of removing the exposed surfaces uniformly reduces a thickness of the liquid crystal display panel.

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